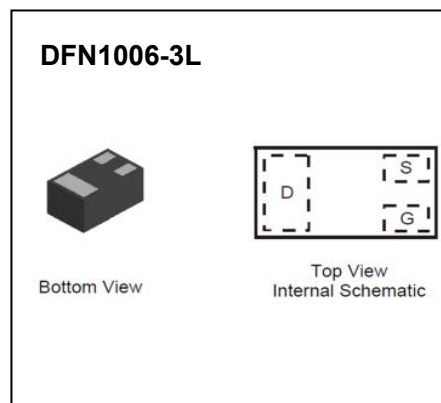


**DFN1006-3L Plastic-Encapsulate MOSFETs****CJBA7002K N-Channel MOSFET**

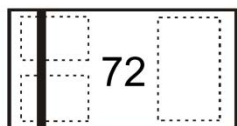
$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
60V	1.5Ω@10V	0.41A
	1.8Ω@4.5V	

**FEATURE**

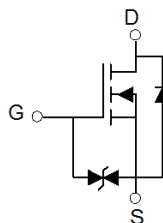
- Low On-Resistance
- Low Threshold Voltage
- Fast Switching Speed
- ESD Protected Gate

APPLICATION

- Load Switch
- Portable Applications
- Power Management Functions

MARKING:

Top View
Bar Denotes Gate
and Source Side

Equivalent Circuit**ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)**

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	$T_a=25^{\circ}\text{C}$	I_D	0.41	A
	$T_a=85^{\circ}\text{C}$		0.30	
Pulsed Drain Current		I_{DM}	1.2	A
Power Dissipation		P_D	0.1	W
Thermal Resistance from Junction to Ambient		$R_{\theta JA}$	1250	$^{\circ}\text{C/W}$
Operation Junction and Storage Temperature Range		T_J, T_{STG}	-55~ +150	$^{\circ}\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS

MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

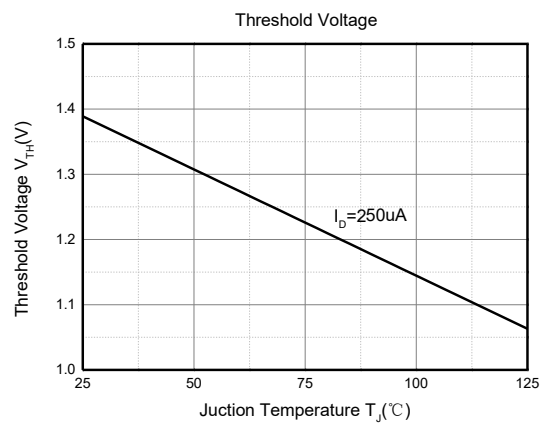
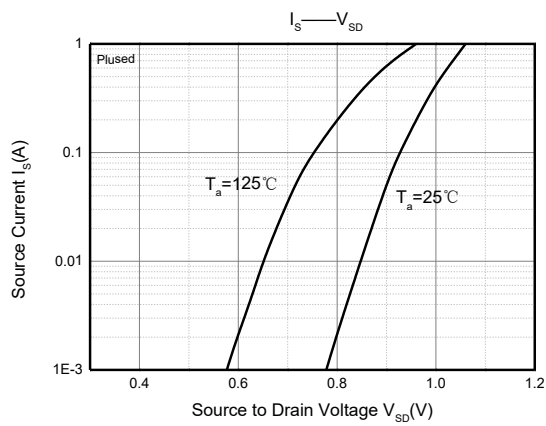
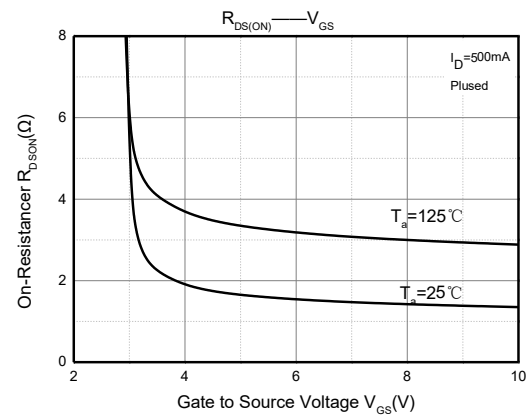
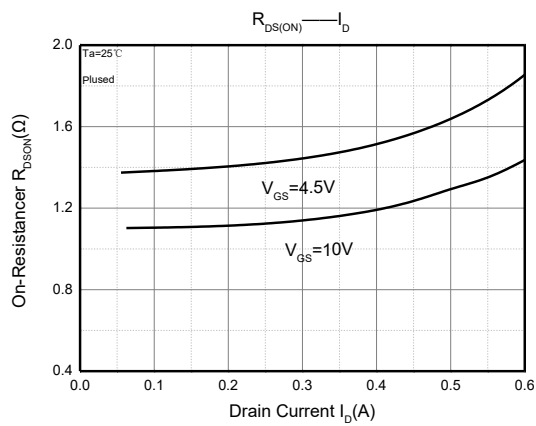
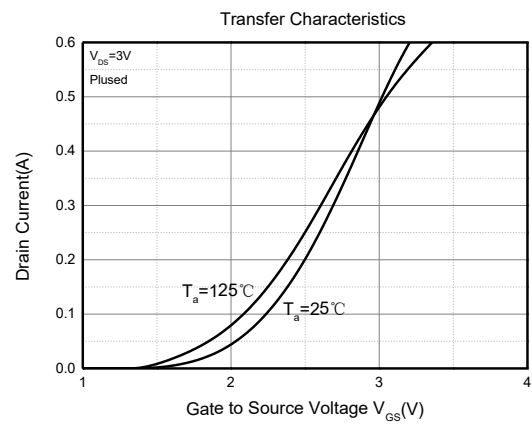
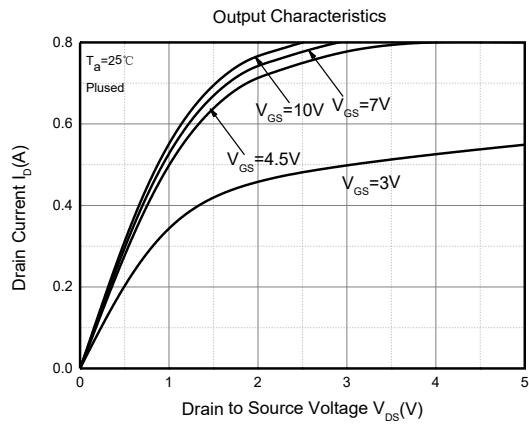
Parameter	Symbol	Test Condition		Min	Type	Max	Unit
Static Characteristics							
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA		60			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =60V,V _{GS} = 0V				100	nA
Gate-body leakage current	I _{GSS}	V _{GS} =±20V, V _{DS} = 0V				±10	μA
		V _{GS} =±5V, V _{DS} = 0V				±1	
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA		1.3	1.4	2.3	V
Drain-source on-resistance ^a	R _{DS(on)}	V _{GS} =10V, I _D =40mA			1.2	1.5	Ω
		V _{GS} =4.5V, I _D =35mA			1.3	1.8	
Forward tranconductance ^a	g _{fs}	V _{DS} = 5V, I _D = 40mA		100			mS
Diode forward voltage	V _{SD}	V _{GS} =0V, I _S =300mA			0.84	1.1	V
Dynamic characteristics							
Input Capacitance ^b	C _{iss}	V _{DS} =40V,V _{GS} =0V,f =1MHz			41	80	pF
Output Capacitance ^b	C _{oss}				3.6	7	
Reverse Transfer Capacitance ^b	C _{rss}				2.9	5.6	
Gate resistance	R _g	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz			81	200	Ω
Total Gate Charge	Q _g	V _{GS} =4.5V			0.72	1.5	nC
		V _{GS} =10V V _{DS} = 50V, I _D = 0.41A			1.41	2.8	
Gate-Source Charge	Q _{gs}				0.24	0.4	
Gate-Drain Charge	Q _{gd}				0.24	0.5	
Turn-on delay time ^b	t _{d(on)}	V _{DS} =30V,RL=50R, V _{GS} =10V,RG=6Ω			3.98	10	ns
Turn-on rise time ^b	t _r				4.95	10	
Turn-off delay time ^b	t _{d(off)}				18.52	40	
Turn-off fall time ^b	t _f				11.94	25	

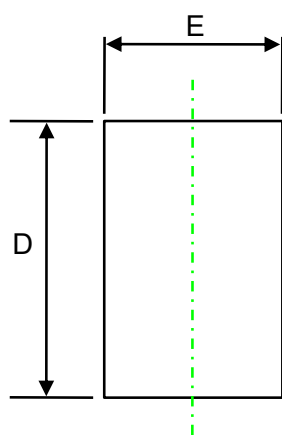
Notes:

a. Pulse Test : Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

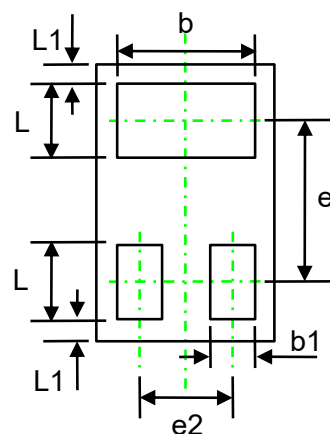
b. These parameters have no way to verify.

Typical Characteristics

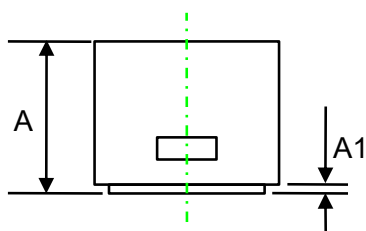




TOP VIEW



BOTTOM VIEW



SIDE VIEW

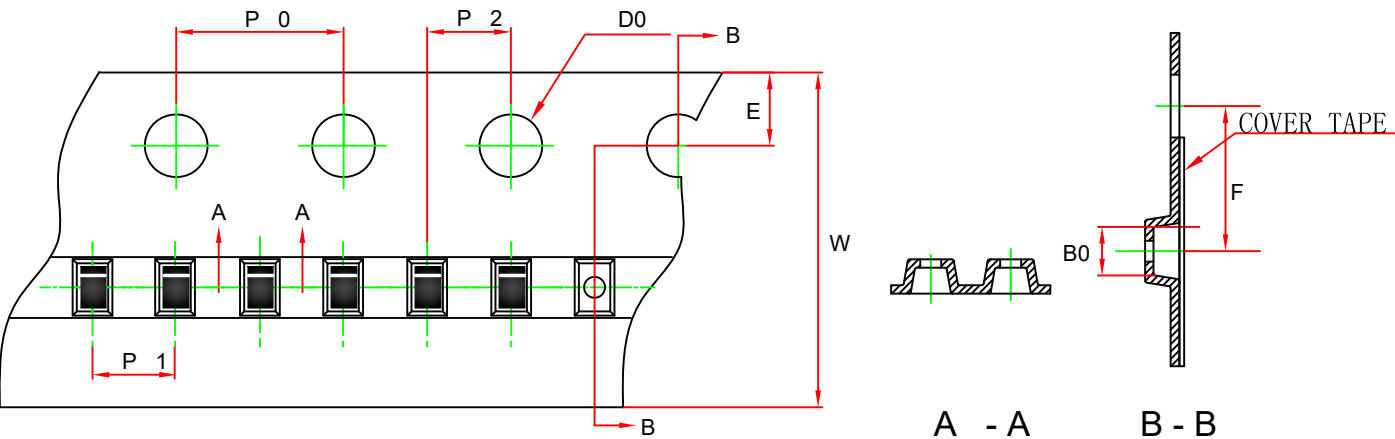
Symbol	Dimensions In Millimeters (mm)		
	Min.	Typ.	Max.
A	0.40	0.47	0.55
A1	0.00	0.03	0.05
D	0.95	1.00	1.05
E	0.55	0.60	0.65
b	0.45	0.50	0.55
e	-	0.65	-
e2	-	0.35	-
L1	0.05 REF.		
L	0.20	0.25	0.30
b1	0.10	0.15	0.20

NOTICE

JSCJ reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. JSCJ does not assume any liability arising out of the application or use of any product described herein.

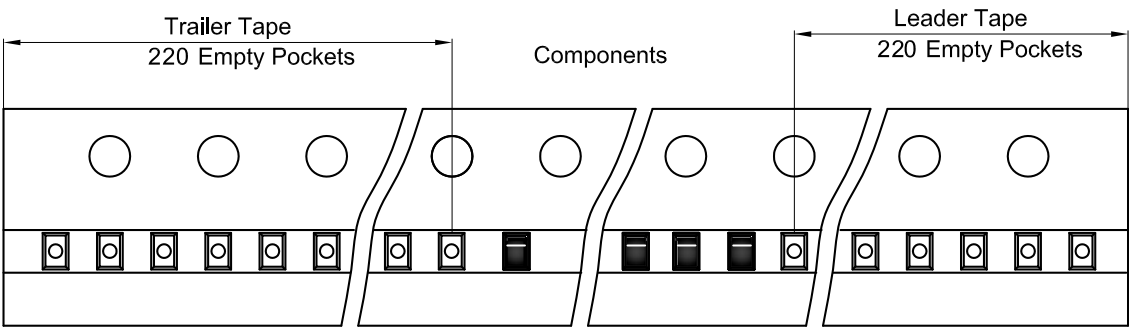
DFN1006-3L Tape and Reel

DFN1006-3L Embossed Carrier Tape

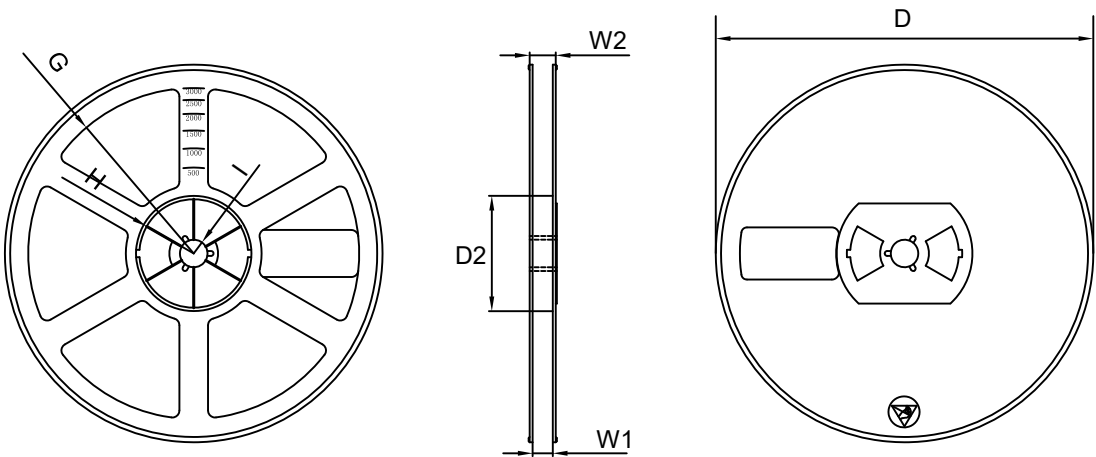


Dimensions In Millimeters (mm)								
Pkg type	B0	P0	P1	P2	E	F	W	D0
DFN1006-3L	1.11	4.00	2.00	2.00	1.75	3.50	8.00	1.55
Tolerance	+/-0.06	+/-0.1	+/-0.1	+/-0.1	+/-0.1	+/-0.1	+/-0.3	+/-0.1

DFN1006-3L Tape Leader and Trailer



DFN1006-3L Reel



Symbol	Dimensions In Millimeters (mm)						
	D	D2	G	H	I	W1	W2
7" Dia	Φ178.00	54.50	R78.00	R25.6	R6.5	9.50	12.30
Tolerance	+/-2	+/-1	+/-1	+/-1	+/-1	+/-2	+/-1.5

REEL	Reel Size	Box	Box size(mm)	Carton	Carton Size(mm)
10000 pcs	7 inch	150000 pcs	220×220×210	6 00000 pcs	450×450×240